

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	23918	spacer near2 (second! another addition\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:35
L2	372364	si?n? or "si.sub.3 or n.sub.4" or nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:03
L3	5351	spacer near2 2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:55
L4	64	(dry plasma pe) near2 etch\$4 near2 3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:54
L5	205622	mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:06
L6	33	4 and 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:06
L7	32	6 and (@ad < "20040227")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:59
L14	2	"20030235966".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:24
L15	105710	(dry plasma pe) near2 etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:25
L16	1	14 and 15	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:25

L17	2237	(dry plasma pe) near2 etch\$4 near2 2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:35
L18	279	17 and 3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:35
L19	117	17 and 3 and 1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:35
L20	638	1 near4 2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:36
L21	48	20 and 17 and 1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:36
L22	46	21 and (@ad < "20040227")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:36
L23	2237	(dry plasma pe) near2 etch\$4 near2 2	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:54
L24	131	3 and 23 and 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:54
L25	129	24 and (@ad < "20040227")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:54
L26	3900081	remov\$4 (spacer 2) near4 (plasma dry pe rie)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:57

L27	4596	26 and 3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:56
L28	3896307	remov\$4 (spacer near2 2) near4 (plasma dry pe rie)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:56
L29	2460	remov\$4 near4 (spacer 2) near4 (plasma dry pe rie)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:57
L30	380	29 and 3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:57
L31	2445131	(wet acid hf hydrofluor\$6 hydro adj fluor\$6 hydro-fluor\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:57
L32	1459063	sio? or "sio.sub.2" or oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:58
L33	45048	31 near2 32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:59
L34	57	30 and 33	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:59
L35	55	34 and (@ad < "20040227")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 16:00
L36	4974	((438/303) or (438/305) or (438/595) or (438/710) or (438/756)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/21 16:41

S95	201409	mosfet or (metal adj oxide adj semiconductor adj (fet or field)) or pmos or cmos or nmos or misfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:06
S96	23390	spacer near2 (second! another addition\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:03
S97	4	(S95 and S96).ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 15:56
S98	234	(S95 and S96).ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/29 15:56
S99	30122	spacer near2 (second! another addition\$4 outer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 18:24
S100	3860	(dry or plasma) near2 etch\$4 near2 (second! another addition\$4 outer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 18:39
S101	3861	(dry plasma pe) near2 etch\$4 near2 (second! another addition\$4 outer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:05
S102	2115	(wet acid hf hydrofluor\$6 hydro adj fluor\$6 hydro-fluor\$4) near2 etch\$4 near2 (second! another addition\$4 outer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 18:39
S103	24	S99 and S101 and S102	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 18:38
S104	1275	S99 near4 (remov\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 11:34

S10 5	105550	(dry or plasma) near2 etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 18:39
S10 6	71848	(wet acid hf hydrofluor\$6 hydro adj fluor\$6 hydro-fluor\$4) near2 etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:57
S10 7	259	S105 and S106 and S104	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/19 18:40
S10 8	253	S107 and (@ad < "20040227")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:07
S10 9	1458111	sio? or "sio.sub.2" or oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 15:58
S11 0	26552	conformal\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 11:30
S11 1	17781	spacer near4 (remov\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 11:34
S11 2	205372	mosfet or (metal adj oxide adj semiconducor adj (fet or field)) or pmos or cmos or nmos or misfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 11:36
S11 3	998	S112 and S110 and S111	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 11:37
S11 4	105586	(dry plasma pe) near2 etch\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 11:36

S11 5	2465	S112 and S110 and S114	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 11:36
S11 6	159	S112 and S110 and S111 same S114	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/21 11:37